

PSMN1R4-40YLD

N-channel 40 V 1.4 m Ω logic level MOSFET in LFPAK56 using NextPower-S3 technology

26 August 2014

Product data sheet

1. General description

Logic level gate drive N-channel enhancement mode MOSFET in 175 °C LFPAK56 package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high performance power switching applications.

2. Features and benefits

- NextPower-S3 technology delivers 'superfast switching with soft recovery'
- Low Q_{RR}, Q_G and Q_{GD} for high system efficiency and low EMI designs
- Schottky-Plus body-diode, gives soft switching without the associated high I_{DSS} leakage
- Optimised for 4.5 V gate drive utilising NextPower-S3 Superjunction technology
- High reliability LFPAK (Power-SO8) package, copper-clip, solder die attach and qualified to 175 °C
- Exposed leads can be wave soldered, visual solder joint inspection and high quality solder joints
- Low parasitic inductance and resistance

3. Applications

- Synchronous rectification
- DC-to-DC converters
- High performance & high efficiency server power supply
- Motor control
- Power OR-ing

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	238	W
Tj	junction temperature			-55	-	175	°C
Static charac	cteristics		'				
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 10		-	1.12	1.4	mΩ



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$	-	1.38	1.85	mΩ
		Fig. 10				
Dynamic char	acteristics					
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 20 V; Fig. 12; Fig. 13	-	13	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 20 V; Fig. 12; Fig. 13	-	45	-	nC

^[1] Continuous current is limited by package.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	[d	G_UN4)
4	G	gate	و و و و	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package	ckage					
	Name	Description	Version				
PSMN1R4-40YLD	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R4-40YLD	1D440L

Limiting values

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	٧
V_{DSM}	peak drain-source voltage	$t_p \le 20 \text{ ns; } f \le 500 \text{ kHz;}$ $E_{DS(AL)} \le 200 \text{ nJ; pulsed}$		-	45	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	40	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	238	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	100	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	1201	Α
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	НВМ		2	-	kV
Source-drai	n diode		1			
I _S	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1201	Α
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 74 A; R_{GS} = 50 Ω; unclamped; t_p = 0.23 ms; V_{GS} = 10 V; $V_{sup} \le$ 40 V	[2]	-	446	mJ
		V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 25 A; $V_{sup} \le$ 40 V; R_{GS} = 50 Ω; unclamped; t_p = 2.52 ms	[2]	-	1641	mJ

Continuous current is limited by package. Protected by 100% test

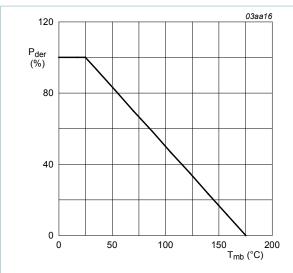
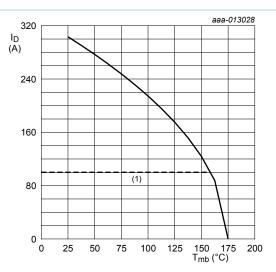


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$



(1) Capped at 100A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

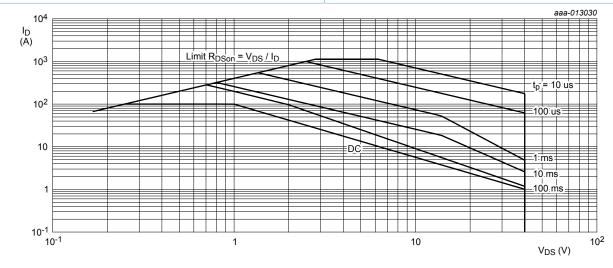


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$ °C; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.56	0.63	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	<u>Fig. 5</u>	-	50	-	K/W
	from junction to ambient	Fig. 6	-	125	-	K/W

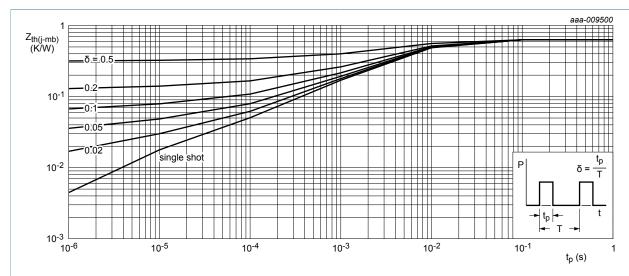


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

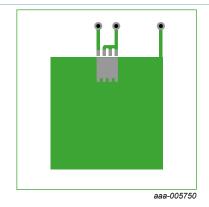


Fig. 5. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper

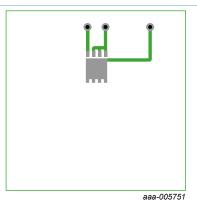


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

10. Characteristics

Table 7. Characteristics

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
V _{(BR)DSS} drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		40	-	-	V	
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$		36	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$		1.05	1.7	2.2	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-4.8	-	mV/K
I _{DSS}	drain leakage current	V_{DS} = 32 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
		V _{DS} = 32 V; V _{GS} = 0 V; T _j = 125 °C	-	12	-	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.12	1.4	mΩ
	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 10	-	-	2.65	mΩ	
		V_{GS} = 4.5 V; I_{D} = 25 A; T_{j} = 25 °C; Fig. 10	-	1.38	1.85	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 10	-	-	3.4	mΩ
R_G	gate resistance	f = 1 MHz	-	1.1	-	Ω
Dynamic cha	aracteristics			'		
Q _{G(tot)} total gate charge	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	96	-	nC	
		I _D = 25 A; V _{DS} = 20 V; V _{GS} = 4.5 V; Fig. 12; Fig. 13	-	45	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	85	-	nC
Q_{GS}	gate-source charge	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 4.5 V;	-	15	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	9	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	6	-	nC
Q_{GD}	gate-drain charge		-	13	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I _D = 25 A; V _{DS} = 20 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	2.7	-	V
C _{iss}	input capacitance	V _{DS} = 20 V; V _{GS} = 0 V; f = 1 MHz;	-	6661	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	1543	-	pF
C _{rss}	reverse transfer capacitance		-	299	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R_L = 0.8 Ω ; V_{GS} = 4.5 V;	-	39	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	49	-	ns
t _{d(off)}	turn-off delay time		-	47	-	ns
t _f	fall time	1	-	30	-	ns

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	50	-	nC
Source-dra	ain diode						
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	47	-	ns
Q _r	recovered charge	V _{DS} = 20 V; <u>Fig. 16</u>	[1]	-	61	-	nC
t _a	reverse recovery rise time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; Fig. 16$		-	25.4	-	ns
t _b	reverse recovery fall time			-	21.7	-	ns

[1] includes capacitive recovery

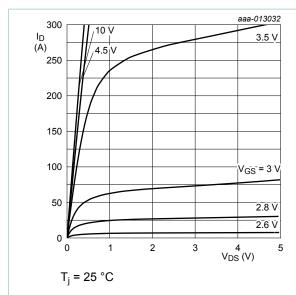


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

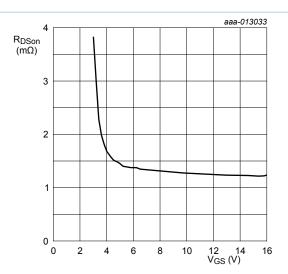


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; \ I_D = 25A$$

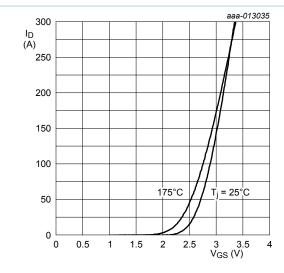


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

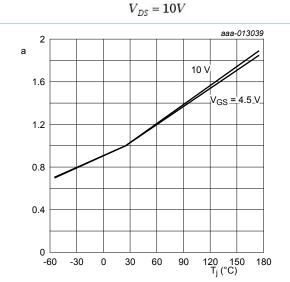


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

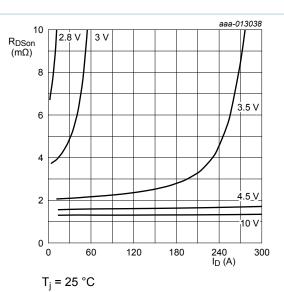


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

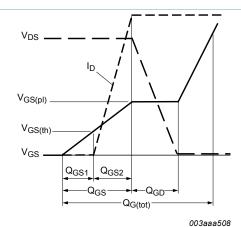


Fig. 12. Gate charge waveform definitions

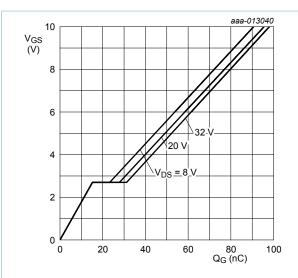


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; \ I_D = 25A$$

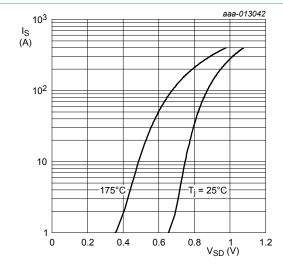


Fig. 15. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

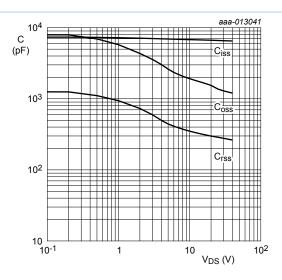


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

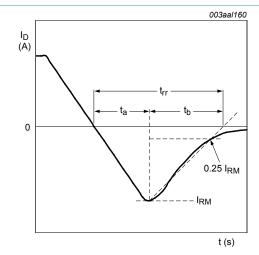
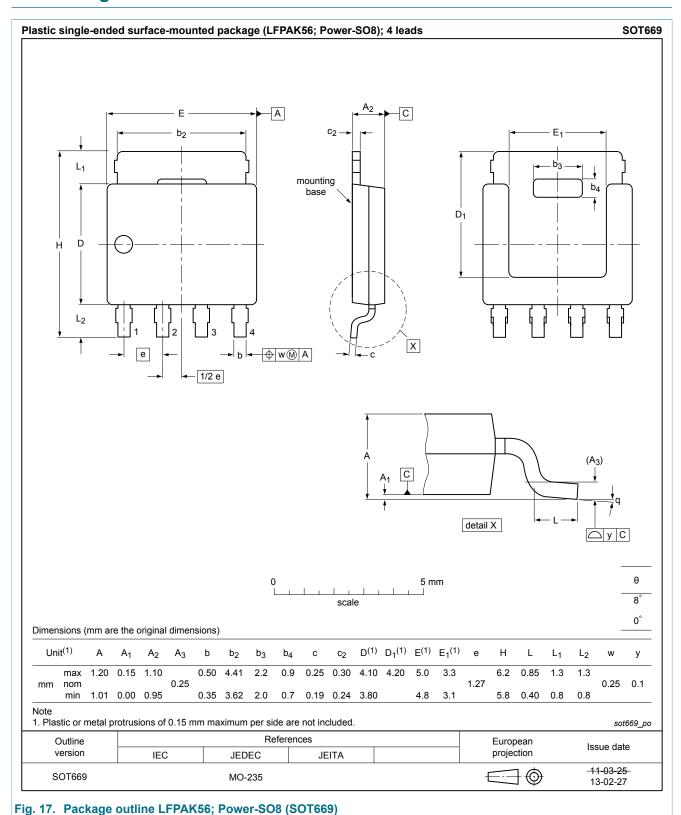


Fig. 16. Reverse recovery timing definition

11. Package outline



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